

2SD1323

Silicon NPN Triple-Diffused Planar Darlington Type

Medium Speed Power Switching

Features

- 30V Zener diode built-in between C and B
- Very small fluctuation in breakdown voltages
- Large energy handling capability
- High speed switching
- "Full Pack" package for simplified mounting on a heat sink with one screw

Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit	
Collector-base voltage	V_{CB0}	30 ± 5	V	
Collector-emitter voltage	V_{CE0}	30 ± 5	V	
Emitter-base voltage	V_{EB0}	5	V	
Peak collector current	I_{CP}	8	A	
Collector current	I_C	4	A	
Collector power dissipation	P_C	Tc = 25 °C	40	W
		Ta = 25 °C	2	
Junction temperature	T_j	150	°C	
Storage temperature	T_{stg}	-55 ~ +150	°C	

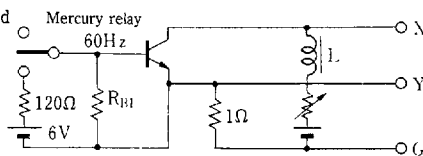
Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 25 V, I_E = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5 V, I_C = 0$			2	mA
Collector-emitter voltage	V_{CE0}	$I_C = 5 mA, I_B = 0$	25		35	V
DC current gain	h_{FE1}	$V_{CE} = 3 V, I_C = 0.5 A$	1000			
	h_{FE2}^{*1}	$V_{CE} = 3 V, I_C = 3 A$	1000		10000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3 A, I_B = 12 mA$			2.5	V
		$I_C = 5 A, I_B = 20 mA$			4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 3 A, I_B = 12 mA$			2.5	V
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 0.5 A, f = 1 MHz$		20		MHz
Turn-on time	t_{on}	$I_C = 3 A, I_{B1} = 12 mA, I_{B2} = -12 mA$ $V_{CC} = 20 V$		0.3		μs
Storage time	t_{str}			3		μs
Fall time	t_f			1		μs
Energy handling capability	$E_{s/10}^{*2}$	$I_C = 2 A, L = 100 mH, R_{Bf} = 100 \Omega$	200			mJ

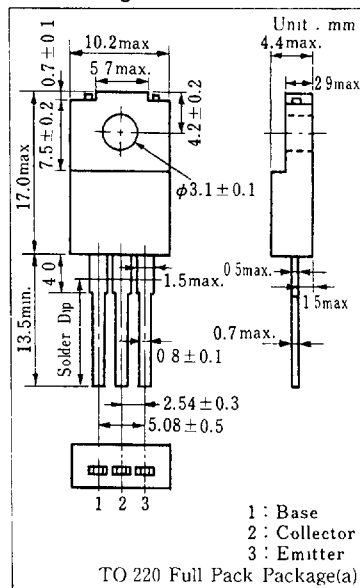
*1 h_{FE2} Classifications

Class	R	Q	P
h_{FE2}	1000 ~ 2500	2000 ~ 5000	4000 ~ 10000

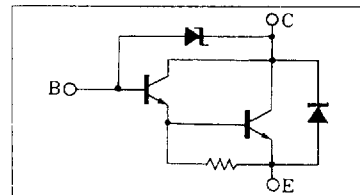
*2 E, b Test method



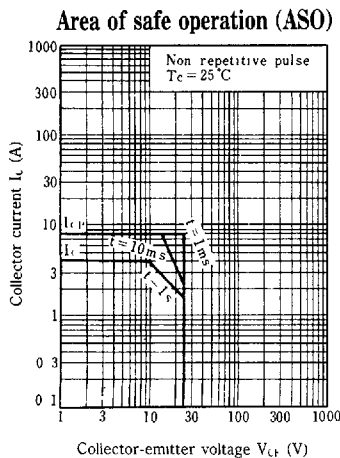
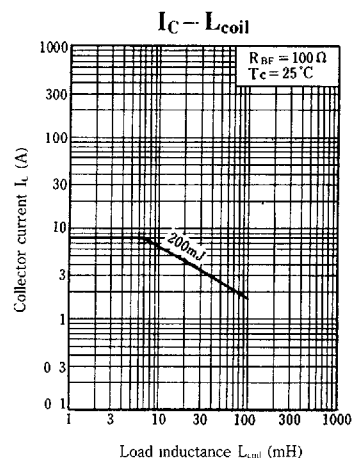
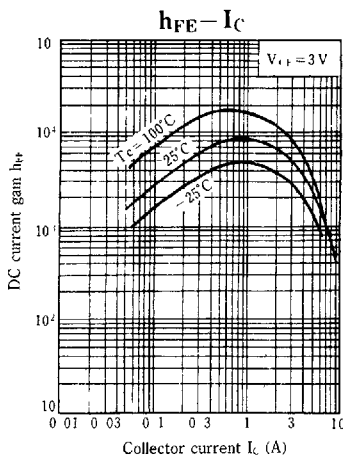
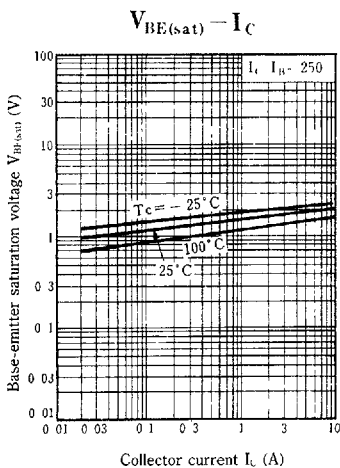
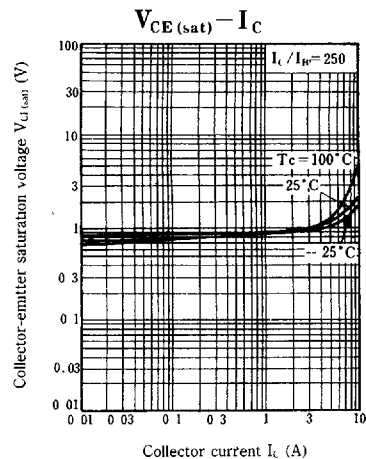
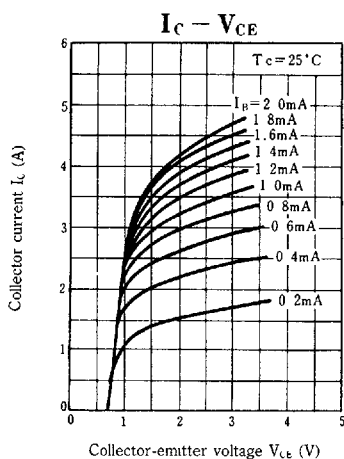
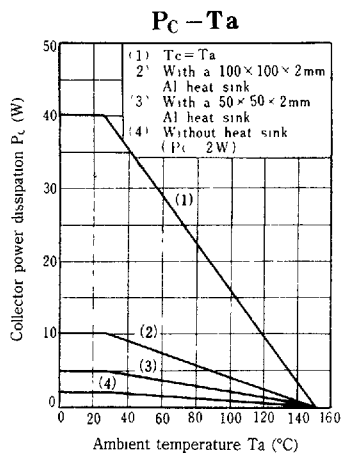
Package Dimensions



Inner Circuit



6932852 0016702 417



6932852 0016703 353